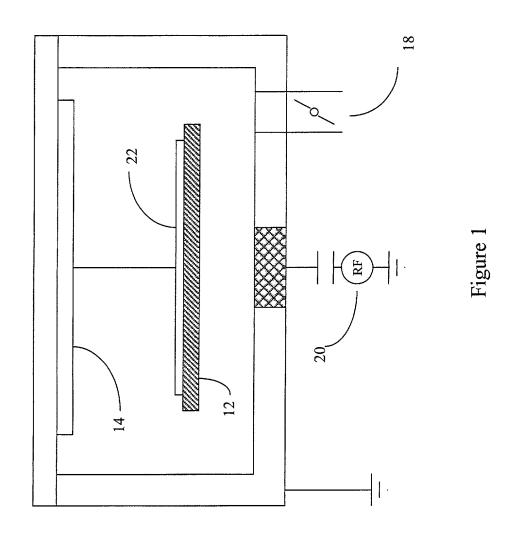
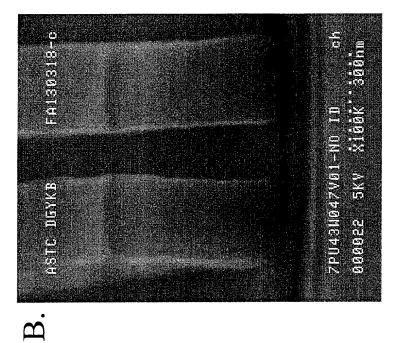
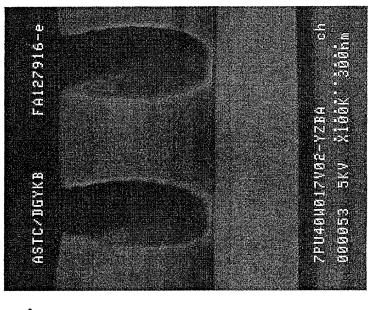
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SiCOH low k dielectric film formed from 3MS and non-nitrogen containing oxidant



SiCOH low k dielectric film formed from 3MS and N_2O oxidant

Figure 2

A

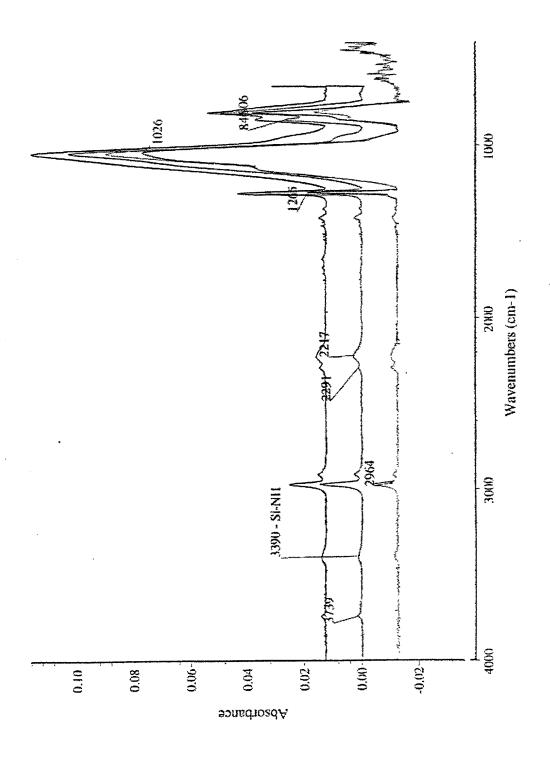


Figure 3

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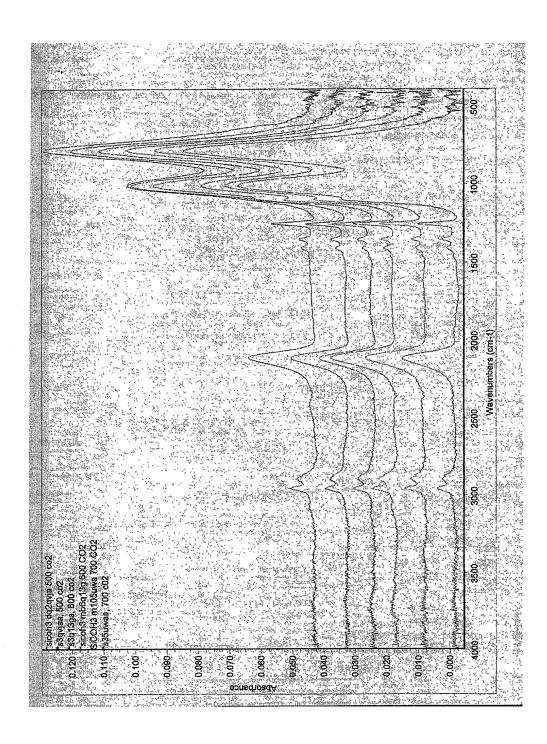


Figure 4